# H all resistance and Lorentz ratio m odels in Y B $a_2$ C $u_3$ O $_7$

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Two-dimensionalm odels of heat capacity, conductivity (), H all resistance ( $R_{\rm H}$ ) and the Lorentz ratio (L) have been derived using the ionization energy ( $E_{\rm I}$ ) based Ferm i-D irac statistics (iFDS) for overdoped Cuprates. These models reproduce the experimentally measured (T) and  $R_{\rm H}$  (T). The variation of L is weakly T-dependent due to the experimental (T). The e-ph coupling in the electrical resistivity has the polaronic e ect that complies with iFDS, rather than the e-ph scattering, which satis es the B loch-G runeisen form ula. These models are purely Ferm i liquid and are not associated with any m icroscopic theories of high-T<sub>c</sub> superconductors.

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#### 1. Introduction

The electrical properties of high-T<sub>c</sub> C uprate superconductors (HTSC) are intrinsically enigmatic in both experim ental and theoretical fram ew ork com pared to other oxide compounds, including manganites. Partly due to its huge potential in a wide variety of applications, intense focus is given on the nature of conductivity of these m aterials to shed som e light on the puzzling tem peraturedependence issues in heat capacity (C), heat conductivity, resistivity, Hall resistance and Lorentz ratio. The con ict in term of T-dependency between and R<sub>H</sub> is also one of the unsolved mystery in HTSC. Even though this paper does not solve it m icroscopically, but it points out that the Ferm i liquid with strong correlations is not downright incorrect, at least for over- and optimally doped HTSC. A part from HTSC, the applications of ionization energy (E, ) based Ferm i-D irac statistics (FDS) on ferrom agnets, diluted ferrom agnetic sem iconductors and doped ferroelectrics have been derived and discussed analytically [1, 2, 3, 4, 5, 6, 7]. The FDS in HTSC have been successfully exploited [1, 2, 3] via the experimental data reported in the Refs. [8, 9, 10, 11, 12, 13, 14, 15, 16, 17, 18, 19]. Recently, the said puzzling T dependencies as well as the spin gap phenom enon have been tackled with the coupling of FDS and charge spin separation [20, 21, 22]. Unfortunately, the pure charge-spin separation, is believed to have serious shortcomings [23, 24, 25, 26, 27]. In addition, there are also num erous experim ental reports with controversial interpretations surrounding the spin P seudogap phenom enon [22, 28, 29, 30, 31, 32, 33, 34]. As such, by ignoring the spin P seudogap phase, the therm om agneto-electronic properties of Y B a<sub>2</sub>C u<sub>3</sub>O 7 w ill be discussed based on the FDS by heavily relying on the basic transport experiments such as the resistivity, Hall resistance, heat capacity and heat conductivity. It is interesting to note that these purely Ferm i-liquid m odels are able to reproduce the related experim ental data reasonably well even if they are only for over- and optim ally doped HTSC. The polaronic e ect that arises as a result of FDS is solely due to heavier e ective m ass e ect, which could indicate the existence of polarons. But this indication is just an extrapolated assumption since heavy electrons do not necessarily form polarons.

### 2. Theoretical details

The free particle H am iltonian of m ass m m oving in 3dim ensions is given by

$$\hat{H} = \frac{\hat{p}^2}{2m} = -\frac{\lambda^2}{2m}r^2$$
: (1)

Here, we have make use of the linear momentum operator,  $p = i \sim r$ . Subsequently, one can write the timeindependent Schrödinger equation for the same particle, how ever in an unknown potential, V (x) as

$$\frac{2}{2m}r^{2}r' = (E + V(x))r'$$
$$= (E_{0})r':$$
(2)

In the second line of Eq. (2), one can notice that the in uence of the potential energy on the total energy of that particular particle has been conveniently param eterized as . This energy function, will be characterized later in such a way that one can replace E + V (x) with  $E_0 +$  in which,  $E_0 = E$  at T = 0. Add to that, from Eq. (2), it is obvious that the magnitude of is given by  $= E = E_0 + V (x)$ . Physically, it in plies the energy needed to overcom e the potential energy as well as the

needed to overcome the potential energy as well as the bound state. Literally, this is exactly what we need to know in any condensed matter, i.e., this magnitude is the one that actually or reasonably de nes the properties of the quasiparticles. Subsequently, we obtain

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$$r^{2}' = \frac{2\pi}{2} \mathbb{E}_{0} \qquad ]':$$
 (3)

$$\frac{-2^{2}k^{2}}{2m} = E_{0} \qquad = \frac{-2}{2m} [k_{0}^{2} \qquad k^{2}]: \qquad (4)$$

 $k^2 = (2m = 2) \mathbb{E}_0$ ]. E and  $E_0$  in a given system range from +1 to 0 for electrons and 0 to 1 for holes that eventually explains the sign in . Now, Eq. (2) can be solved to give

$$' = C_{N}$$

$$\exp [i(k_{0;x} \quad k_{;x})x + i(k_{0;y} \quad k_{;y})y + i(k_{0;z} \quad k_{;z})z]:$$

$$'_{k_{(0; )}} = C_{N} e^{ik_{(0; )}} \stackrel{r}{:} (5)$$

 $k^{2} = (k_{0,x}^{2} \quad k_{ix}^{2}) + (k_{0,y}^{2} \quad k_{iy}^{2}) + (k_{0,z}^{2} \quad k_{iz}^{2}).$  By em ploying the orthonorm ality and Plancherel's theorem, one can nd the norm alization constant, C N by com paring Eqs. (6) and (7) as shown below.

$$Z Z Z$$

$$h'_{k_0} j'_{k_0} k i = '_{k_0} k_{0} k dxdydz$$

$$= C_N^2 e^{i(k_0 (k_0 k))} dxdydz$$

$$= (k): (6)$$

$$\frac{1}{(2)^{3}} \sum_{x=1}^{Z} \sum_{x=1}^{Z} e^{ik_{0}} (r \hat{r}) dk_{x} dk_{y} dk_{z} = (r \hat{r}): (7)$$

Hence,  $C_N = 1 = (2)^{3=2}$ . nally, the normalized wave function, which corresponds to Eq. (2) is

$$'_{k(0;)} = \frac{1}{(2)^{3=2}} e^{i[k(0;)]}$$
 (8)

In a physical sense as stated earlier,  $= E = E_0 + V(x)$ , is in an identical scale with the energy needed to free an electron from an atom in a given crystal. As such, we apply the concept of ionization energy where,  $= E_{\tau}^{real}$ =  $E_I + V(x)$ , to justify that an electron to occupy a higher state N from initial state M is more probable than from initial state L if condition  $E_{I}(M) < E_{I}(L)$  at certain T is satis ed. As for a hole to occupy a lower state M from initial state N is more probable than to occupy state L if the same condition above is satis ed. It is well known that the exact values of E  $_{\rm I}$  are known for an isolated atom . In this case (for an isolated atom ),  $E_{T}$  can be evaluated with

$$E_{I} = \frac{X^{Z}}{\sum_{i} \frac{E_{Ii}}{Z}}$$
(9)

However, substituting the same atom in a crystal gives rise to the in uence of V (x) and in reality, E  $_{\rm T}^{\rm real}$  cannot be evaluated from Eq. (9). Nevertheless, the  $E_{T}^{real}$  of an atom or ion in a crystal is proportional to the isolated atom and/or ion's E  $_{\rm I}$  as written below .

$$E_{I}^{real} = \frac{X^{Z}}{i} \frac{E_{Ii}}{Z}$$
$$= E_{I}:$$
(10)

It is this property that enables one to predict the variation of electronic properties of superconductors with substitution reasonably well. The constant of proportionality, is a function of averaged V (x) and varies with dierent background atoms. For example, in  $YBa_1 xCa_xCu_2O_7$  system,  $YBa_1 x-Cu_2O_7$  de nes the background atom s or ions. Therefore, one needs to em ploy the experim ental data to determ ine the magnitude of  $= E_{T}^{real} = E_{T} + V(x)$ .

Recall that Eq. (4) simply implies that the one-particle energies E1, E2, ..., Em for the corresponding oneparticle quantum states  $q_1, q_2, ..., q_n$  can be rewritten as (E o  $E_{I}$ )<sub>1</sub>, ( $E_{0}$   $E_{I}$ )<sub>2</sub>, ..., ( $E_{0}$  $\mathrm{E}_{\mathrm{I}}$ )<sub>m</sub> . It is also important to note that  $E_0 + E_I = E_{electrons}$  and  $E_0$  $E_{I} = E_{holes}$ . As such, for n particles, the total num ber of particles and its energies are conserved and the conditions to ful 11 those conservations are given by

Subsequently, the Ferm i-D irac statistics based on ionization energy can be derived as

$$\frac{n_i}{q_i} = \frac{1}{\exp[+(E_0 - E_I)_i] + 1}$$
(13)

By utilizing Eq. (13) and taking  $\exp[+(E E_T)]$ 1, one can arrive at the probability function for electrons in an explicit form as

$$f_e = \exp \frac{-k_0^2 k_0^2}{2m} + E_I$$
; (14)

Sim ilarly, the probability function for the holes is given by

$$f_h = \exp + \frac{\sim^2 k_0^2}{2m} E_I$$
 : (15)

The parameters and are the Lagrange multipliers. ~ = h=2, h = P lanck constant and m is the charge carriers' mass. In the standard FD S, Eqs. (14) and (15) are simply given by,  $f_e(k) = \exp[(-c^2k^2=2m)]$  and  $f_h(k) = \exp[+(-c^2k^2=2m)]$  respectively.

Subsequently Eq. (11) can be rewritten by employing the 2D density of states' (DOS) derivative, dn =  $L^2k_0dk_0=2$ , Eqs. (14) and (15), that eventually give

$$n = \frac{L^2}{2} e^{\sum_{i=1}^{Z} k_0} \exp \frac{-\frac{k_0^2}{2m}}{2m} dk_0; \quad (16)$$

$$p = \frac{L^2}{2} e^{\sum_{i=1}^{Z^0} k_0} \exp \left( \frac{-k_0^2 k_0^2}{2m} \right) dk_0 : \quad (17)$$

Note here that  $E_0$  is substituted with  ${^2k_0^2/2m}$ . n and p are the respective concentrations of electrons and holes.  $L^2$  denotes area in k-space. The respective solutions of Eqs. (16) and (17) are given below

$$e^{+E_{I}} = \frac{mL^{2}}{2n \sim 2};$$
 (18)

$$e^{E_{I}} = \frac{2p^{2}}{mL^{2}};$$
 (19)

Equations (18) and (19) respectively imply that

$$_{e}$$
 (iF D S) =  $_{e}$  + E  $_{I}$ ; (20)

$$_{h}$$
 (iF D S) =  $_{h}$  E<sub>I</sub>: (21)

0 n the other hand, using Eq. (12), one can obtain

$$E = \frac{L^{2} \sim^{2}}{4m} e^{\sum_{i=1}^{2} k_{0}^{3}} \exp \frac{-\frac{\sqrt{2}k_{0}^{2}}{2m}}{2m} dk_{0}$$
$$= \frac{m}{2} \frac{L}{\sqrt{2}} e^{\sum_{i=1}^{2} \frac{1}{2m}} e^{\sum_{i=1}^{2} \frac{1}{2m}} dk_{0}$$
(22)

Equation (22), after appropriate substitution with Eq. (18) is compared with the energy of a 2D ideal gas,  $E = nk_B T$ . Quantitative comparison will eventually leads to  $_{iFDS} = _{FDS} = 1/k_B T$  where  $k_B$  is the Boltz-mann constant. The distribution function for electrons and holes can be written explicitly by rst denoting =

 $E_F$  (Ferm i level), =  $1/k_B T$  and substituting these into Eqs. (14) and (15) will lead one to write

$$f_{e}(E; E_{I}) = \exp \frac{E_{F} E_{I} E}{k_{B} T}$$
 : (23)

$$f_{\rm h} (E; E_{\rm I}) = \exp \frac{E E_{\rm I} E_{\rm F}}{k_{\rm B} T}$$
 : (24)

Note that Eqs. (20) and (21) simply imply that  $_{e}$  (iFDS) = (T = 0) + E  $_{I}$  and  $_{h}$  (iFDS) = (T = 0)  $E_{I}$ . In fact, (FDS) need to be varied accordingly with doping, on the other hand, iFDS captures the sam e variation due to doping with  $E_{I}$  in which, (T = 0) is xed to be a constant (independent of T and doping). Furtherm ore, using Eqs. (4), (12) and (22), one can obtain

$$E_{iFDS} = \frac{L^{2} \kappa^{2}}{4m} e^{\sum_{i=1}^{2} k_{0}^{3}} \exp \frac{-\frac{\kappa^{2} k_{0}^{2}}{2m}}{2m} dk_{0}$$

$$= \frac{L^{2} \kappa^{2}}{4m} e^{\sum_{i=1}^{2} k_{0}^{3}} \exp \frac{-\frac{\kappa^{2} k_{0}^{2}}{2m}}{2m} \frac{-\frac{\kappa^{2} k^{2}}{2m}}{2m} dk_{0}$$

$$= \frac{L^{2} \kappa^{2}}{4m} e^{\sum_{i=1}^{2} k_{0}^{3}} \exp \frac{-\frac{\kappa^{2} k^{2}}{2m}}{2m} dk$$

$$= E_{FDS}: \qquad (25)$$

Eventually, Eq. (25) proves that the total energy of n particles considered in both FDS and  $\pm$ DS is exactly the sam e.

### 3. Heat capacity and its conductivity

E lectrons and phonons can be excited to a higher energy levels satisfying the ionization energy based Ferm i-D irac ( $f_{iFDS}$  (E)) and Bose-E instein  $f_{BES}$  (E) statistics respectively. Therefore, the heat capacity can be explicitly written as

$$C = \frac{m}{\sim^{2}} (E E_{F} E_{I}) \frac{(e_{I_{F} D S} (E))}{(e_{T})} dE$$

$$+ \frac{Z}{(E} E_{F}) \frac{(e_{I_{B} E S} (E))}{(e_{T})} dE : (26)$$

~ = h=2, h denotes P lanck constant, while m represents the elective mass. The respective distribution functions for BES and iFDS (using Eq. (4)) are given by  $f_{B E S}(E) = 1 = [exp (E E_F) = k_B T 1] exp (E_F E) = k_B T and f_{iF D S}(E) = 1 = [exp (E E_F + E_I) = k_B T + 1] exp (E_F E_I E) = k_B T . These approximations$ 

are necessary to avoid the exponential integral function,  $_{i}(z) = \int_{z}^{1} [e^{t} = t] dt$ , which has a branch cut discontinuity in the complex z plane running from 1 to 0. Additionally, I highlight that for classical particles satisfying the M axwell-Boltzm ann statistics (M B S), there is no such thing as  $E_{I}$ . Consequently, one should not assume that exp[ + (E in itial state E<sub>T</sub>)] 1 should give the M B distribution function as a classical or a free-electron lim it. One can indeed arrive at MBS by rst considering the additional constraint,  $E_{I} = 0$  in such cases, where E<sub>total</sub> now equals to E identical with the standard FDS and MBS. Therefore, the electron's Ferm i level,  $E_F$  term that contained in  $f_{B E S}$  (E) corresponds to the phonons' energies above this E  $_{\rm F}$  , in which this E  $_{\rm F}$  does not im ply phonons' chem ical potential. In other words, phonons with energies  $< E_F$  are neglected. In summary, iFDS captures the Fermiliquid (€ 0) rather than the Fermi gas (V (x) = 0).

The total heat capacity in Eq. (26) has been written as  $C =_P C^e + C^{ph}$  as a pesult of the total heat current,  $= j_0 (r T)^{-1} = C v_F^2 = 2$ . = electron (e), phonon (ph) and  $= e \cdot e$ ,  $e \cdot ph$  scattering.  $v_F$  denotes the Ferm i velocity and  $k_B$  is the Boltzm ann constant. Im portantly, E<sub>I</sub> is m icroscopically de ned as [7]

$$(0;k) = 1 + \frac{K_s^2}{k^2} \exp (E_F^0 - E_I)$$
: (27)

(0;k) is the static dielectric function, k and % k are the wavevector and Lagrange multiplier respectively. The  $E_{F}^{0}$  denotes the Ferm i level at 0 K, while the K\_{s} represents the Thomas-Ferm is creening parameter. Unlike electrical resistivity in YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub>, its 2D heat conductivity is equally strongly in uenced by e-e and e-ph interactions, hence (after taking  $E_{F}=\frac{1}{2}m\ v_{F}^{2}$ )

$$= {}_{e \ e} C^{e} \frac{E_{F}}{m} + {}_{e \ ph} C^{ph} \frac{E_{F}}{m_{ph}} :$$
 (28)

The explicit form of Eq. (28) can be obtained after substituting Eq. (26) into Eq. (28) appropriately. The electron-electron scattering rate,  $e^1 e^{-1} = AT^2$  while the electron-phonon scattering rate,  $e_{ph}^{1}$  is assumed to be proportional to T in which > 2. The Ferm i-level in Eqs. (26) and (28) in plies that the phonons considered here have the therm al energies in the order of or higher than the electrons' Ferm i energy which eventually means that these electrons cannot form Fermigas. In simple words, if the therm all energies of the phonons are less than the electrons'  $E_{\rm F}$  , then these electrons can act as Fermigas and one may employ the Debye approximation. This is another reason why Debye model works extrem ely well at interm ediate and low tem peratures in com m on m etals. How ever, the phonons' e ective m ass is equal to the ions reduced m ass due to phonons interaction with free-electrons,  $1=m_{ph} = 1=m_e + 1=m_{ion}$ , which

needs to be determ ined from other techniques, be it theoretical or experim ental. Therefore, only the electron's e ectivem ass is highlighted here. In other words, instead of addressing  $1=m_{\rm ph}$  as the reduced m ass of ions, it has been labelled as phonons e ective m ass so that one can conveniently identify it as the parameter belonging to the phonons' contribution.

#### 4. R esistivity and H all resistance

The equations of motion (EOM) for charge carriers in ab-planes under the in uence of static m agnetic (H) and electric elds (E) can be written in an identical fashion as given in Ref. [35], which are given by m d=dt+ 1=  $_{e}$  v<sub>b</sub> =  $eE_b + eH_cv_a$  and m  $d=dt + 1 = ev_a = eE_a eH_cv_b$ . The charge, e is de ned as negative in the EOM above. M oreover, it is in portant to realize that the existence of electrons in ab-planes below T<sub>crossover</sub> are actually holes. The existence of holes in ab-planes was discussed intensively in the Refs. [36, 37, 38]. The subscripts a, b and c represent the axes in a, b and c directions while the subscript ab represents the ab-planes. In a steady state of a static H and E,  $dv_a = dt = dv_b = dt = 0$  and  $v_a =$ 0 hence one can obtain  $E_a = eH_cE_{be} = m$  . The Hall resistance and current along a- and b-axes are respectively de ned as  $R_{H}^{(a)} = E_{a} = j_{b}H_{c}$ ,  $j_{b} = E_{b} = in which$ ,  $\tan \frac{a}{H} = E_a = E_b$ . Parallel to this,  $R_H^{(a)} = \tan \frac{a}{H} = H_c$ .  $\mathbf{j}_{\mathrm{b}}$  is the current due to holes motion along b-axis and  $_{\rm H}^{\rm (a)}$  is the H all angle in ab-planes. Furtherm ore, one can rewrite tan  $_{\rm H}^{\rm (a)}$  as tan  $_{\rm H}^{\rm (a)}$  = eH  $_{\rm c}$ =m AT  $^2$  , which eventually suggests, cot  $_{\rm H}^{\rm (a)}$  / T  $^2$  . A is  $_{\rm e}$  dependent constant and is independent of T. The 2D resistivity model, (T) is given by [1, 2, 3]

(T) = 
$$A \frac{{\sim}^2}{k_B e^2} T \exp \frac{E_I + E_F}{T}$$
 : (29)

Utilizing Eq. (29), one can show that the Hall resistance is given by

$$R_{\rm H} = \frac{\sim^2}{m \ T \, k_{\rm B} \, e} \exp \frac{E_{\rm I} + E_{\rm F}}{T}$$
 : (30)

Thus, it is clear that  $R_{\rm H}$  is proportional to 1/T regardless of the axes. Detailed analysis and diagnosis of Eq. (29) with a wide variety of experimental data are well documented in the Refs. [1, 2, 3]. Optimally doped YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub> single crystal (A1) obtained from Ref. [39] will be utilized in the following analysis. Equation (29) has been employed to theoretically reproduce (indicated with a solid line in the inset of Fig. 1) the experimental <sub>ab</sub>(T) by varying the T-independent scattering rate constant, A (7.3 10<sup>7</sup> cm) whereas E + E<sub>F</sub> =  $T_{\rm crossover}$   $(T_{\rm cr})$  is taken as 0 K, since any optim ally doped Y B  $_{\rm 22}{\rm Cu}_{3}{\rm O}_7$  gives  $T_{\rm cr}$   $T_{\rm c}$  in which  $T_{\rm cr}$  is not observable from the resistivity m easurements. I.e.,  $T_{\rm cr}$  cannot be predicted accurately from the norm all state resistivity measurements. On the other hand, the  $R_{\rm H}^{\rm (ab)}$  (T) data and the plot using Eq. (30) are depicted in Fig. 1. Note that  $A = A \sim^2 = k_{\rm B} e^2$  from Eq. (29) and  $A_{\rm H} = \sim^2 = m k_{\rm B} e = 347 \ {\rm JKC} \ {\rm s}^2 {\rm kg}^{-1}$  from Eq. (30). In the latter approximation,  $m = 50m_0, m_0$  is the rest mass of the electron. In order to accurately t the experimental  $R_{\rm H}^{\rm (ab)}$  (T) data, the electrom ass should be equal to 73m\_0, which in turn gives the charge carriers density as  $p = 8 - 10^{22} \ {\rm cm}^{-3}$ , in accordance with the Refs. [3, 17].

#### 5. Lorentz ratio

Lanzara et al. [27] have shown that the e-ph coupling is somewhat inevitable, which has been observed via ARPES technique. Indeed this supports the notion of polaronic e ect above  $T_c$  in cuprates. One should note that the observation e-ph coupling does not mean that there is a e-ph scattering since norm al state (T) measurements thus far failed to reveal any e-ph scattering (strong T-dependence). A ctually, this is not because of

(T)'s blindness, but due to polaronic e ect represented by E<sub>I</sub>, which gives rise to the e ective mass (m) of electrons instead of strong T-dependence. The heavier m implies the existence of polaronic e ect in the normal state of HTSC that also suppresses e-ph scattering but not the e-ph coupling in term of polaronic e ect. Sim ilarly, isotope e ect  $(^{18}O, ^{16}O)$  in cuprates [40, 41, 42] also reinforces the polaronic contribution via e-ph coupling rather than e-ph scattering. In fact, H ofer et al. [40] claim ed that m reduces towards the optim ally doped HTSC. This scenario is consistent with iFDS based models that predicts T<sub>cr</sub> also reduces tow ards optim aldoping. Simply put, reduced  $E_{I}$  will eventually lead to reduced m and consequently the in uence of isotope doping on is less e ective in optimally doped regime as com m pared to under doped. The inappropriateness of the e-ph scattering in YBCO<sub>7</sub> will be discussed in detail based on the Bloch-Gruneisen formula shortly. From the de nition, L can be written as

$$L = \frac{1}{T} = A \frac{r^2}{k_B e^2} \exp \frac{E_I + E_F}{T}$$
 (31)

Interestingly, Sutherland et al. [43] have reported only a slight increase (upward deviation) in ab-plane's heat conductivity with phonon contribution ( $\frac{100K}{ab}$  /  $\frac{300K}{ab}$ 

1.3) above critical temperature  $(T_c)$  for overdoped YBCO. Their results will be used to discuss the accuracy of Eqs. (28) and (31) to capture the experimental data.

# 6. e-ph scattering in resistivity

Firstly, the Bloch-Gruneisen (BG) formula will be revisited in order to rule out the e-ph scattering in the norm al state of YBCO7. Recall that the polaronic effect that arises from the E<sub>I</sub> based Ferm i-D irac statistics (FDS) has been successful to explain and predict the evolution of resistivity with doping and to enum erate the m in im um valence state of multivalent dopants in HTSC, ferrom agnets and recently in doped-ferroelectrics. But FDS does not reveal the inadequacy of the free e-ph scattering directly (only indirectly). Basically, according to the e-ph scattering, the electrons from  $Ba^{2+}$  and  $Sr^{2+}$  as in Y (Ba<sub>1 x</sub> Sr<sub>x</sub>)<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub> has the same e ect on transport m easurem ents while IFDS points out that the kinetic energy (KE) of the electrons from  $Ba^{2+}$  is not equalwith the KE of the electrons from Sr<sup>2+</sup>, which gives rise to signi cant changes of resistivity with sm all doping. Again, if one assumes KE ( $Ba^{2+}$ ) = KE ( $Sr^{2+}$ ), then the theory of the e-ph scattering is indeed applicable due to isotropy in KE (all the free electrons have an identical KE, which eventually de nes the Ferm isurfaces). Hence, to further evaluate the incom patibility of the e-ph scattering in YBCO7, the BG formula [44] stated in Eq. 32 is employed to plot the T-dependence of (T) (assuming  $_{\rm e~ph}$  (3D) /  $_{\rm e~ph}$  (2D)) and L(T).

$${}_{BG} = tr \frac{128 \text{ m } k_{B} \text{ T}^{5}}{ne^{2} \frac{4}{D}} \int_{0}^{Z^{-2T}} \frac{x^{5}}{\sinh^{2} x} dx: \quad (32)$$

 $t_{\rm r}$  = electron-phonon coupling constant, m = average e ective mass of the occupied carrier states,  $_{\rm D}$  = D ebye tem perature, n = free electrons concentration. The L (T) can be simply written as

$$L_{BG} = tr \frac{128 \text{ m } k_B T^4}{ne^2 \frac{4}{D}} \int_{0}^{Z^{-2T}} \frac{x^5}{\sinh^2 x} dx: (33)$$

#### 7. A nalysis

Figure 2 a) and b) depict the T-dependence of (T) (Eq. (32)) and L (T) respectively. The L (T) based on BG 's approach after incorporating the experimental are indicated with M ( $_D = 200 \text{ K}$ ), ( $_D = 300 \text{ K}$ ), and t ( $_D = 350 \text{ K}$ ). On the other hand, the experimental and iFDS based theoretical plots (Eqs. (28), (29) and (31)) are shown with and a solid line, respectively in Fig. 2 b). Note that in Eq. (28), = 3 is used complying with the earlier assumption of T  $^{>2}$ . This value is reasonable since in the free e-ph scattering of conventionalm etals are known to vary between 3 and 5, depending on

T's range that can be veried from Eq. (32). The experimentalL(T) is obtained from the resistivity [45] and heat conductivity [43] measurements of optimally doped YBCO.

The inverse proportionality of the theoretically determined with T from Eq. (28) is understandable since the electrical conductivity is proportional to 1=T and there are phonon contribution as well. As a result of this, L (T) is also inversely proportional to T. It is not possible to evaluate Eq. (28) quantitatively due to the unknown m agnitudes of E  $_{\rm I}$  , E  $_{\rm F}$  , m  $_{\rm ph}$  and A  $_{\rm e}$   $_{\rm ph}$  . However, the measured in the norm alstate of YBCO hardly shows strong T dependence [43] indicating the existence of som e not-yet-known physical phenom ena, which com plicates our understanding of HTSC generally. Anyhow, by using the experim entally determ ined , one can verify the accuracy of the resistivity equations (between Eq. (29) and (32)). The former equation is entirely based on e-e scattering while the latter contains the essential eph scattering m echanism. To this end, the lorentz ratio based on FDS (Eq. (31)) and BG (Eq. (33)) are com puted using the alm ost T independent or experim ental

The FDS model reproduces the T dependence trend, rem arkably identical with the experim ental data as opposed to the BG's approach. Both FDS and BG models with the experimental have been plotted in Fig. 2 b), in which the latter model is plotted at different D. Eventually, one can convincingly state that e-ph scattering mechanism is signi cantly negligible in the electrical resistance m easurem ents. The plot that corresponds to Eq. (31) with experimental is obtained using  $E_{T} + E_{F} =$ 10 K , (which is less than  $T_c$  as a result of optim alor over doping) and experimental that eventually give A = 110 8 om . This magnitude is remarkably identical with the optim ally doped crystalline YBCO sample of Hagen et al. [19] and Leridon et al. [45] that have been calculated  $(A_{H agen;Lerridon} = (1.1,1.4)$ 10 <sup>8</sup> and reported in the Refs. [2, 21]. Importantly, even though Eq. (32) can be shown to capture the experim ental T-linear property of (I), but it also fails to explain the T<sub>cr</sub> above  $T_{\rm c}$  for slightly under doped HTSC .  $T_{\rm cr}$  is the T where (T) deviates upward exponentially, which has been well explained [1, 2, 3] via  $E_I$  in Eq. (29).

# 8. C on clusions

In conclusion, iFDS based electrical resistivity (with ee scattering rate only) and heat conductivity (with both e-e and e-ph scattering rate) models have been utilized to tackle the T dependence of Lorentz ratio in optim ally doped YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub>. The computed L (T) with experimental overwhelmingly suggests that B loch-G runeisen form ula or the inclusion of e-ph scattering in the electrical resistivity is not suitable, at least for YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub>. On FIG.1: Experimental  $R_{\rm H}^{\rm (ab)}$  (T) and  $_{\rm ab}$  (T) (inset) data points for YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub> single crystal (A1) have been tted using Eqs. (30) and (29) respectively. The former equation is com – puted with two m snamely, 50m<sub>0</sub> and 73m<sub>0</sub> while the resistivity is calculated with A = 7.3 10<sup>-7</sup> cm.

FIG. 2: a) Shows the BG resistivity, (T) plots above 90 K for  $_{\rm D}$  = 350, 300 and 200 K.W hereas, b) depicts the theoretical plots for the BG Lorentz ratio,  $L_{\rm BG}$  above 90 K with experim ental heat conductivity () using Eq. (33) with the D ebye T,  $_{\rm D}$  = 350, 300 and 200 K. The calculated L (T) with Eq. (31) using experimental is also plotted with in b). The theoretical solid line in b) satis es iFDS based models namely, Eqs. (28), (29) and (31) with = 3. The experimental plots indicated with is obtained from the data combined from Leridon et al. [45] and Sutherland et al. [43].

the other hand, e-ph scattering contributes signi cantly in heat conductivity that eventually gives a reasonably acceptable picture for the experim entalheat conductivity and Lorentz ratio. A dditionally, the spin P seudogap phenom enon have been on itted throughout so as to avoid its inconclusive interpretations. A part from that, the m agnitudes of the T -independent scattering rate constant, effective m ass and the charge carriers density are all in the acceptable range, com plying with other optim ally doped YBCO single crystals as com puted previously.

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